In the Claims:

- 1. (Previously presented) A diamond tool fabricated with a single crystal diamond artificially synthesized under high pressure in a temperature difference method, characterized in that said diamond has a crystal containing an impurity in an amount of at most 3 ppm and the tool has a blade with an end having a plane orientation being a (110) plane.
- 2. (Original) The diamond tool according to claim 1, wherein said crystal contains said impurity in an amount of at most 0.1 ppm.
- 3. (Original) The diamond tool according to claim 1, being one of an ultra high precision cutting tool, a microtome knife, a diamond knife, a diamond stylus, a line drawing die, and a dresser.
- (Currently amended) The diamond tool according to claim 1, wherein a titanium containing, activated brazing material [[(22)]] is employed to attach said diamond to a main body of the tool.
- 5. (Previously presented) A diamond tool fabricated with a single crystal diamond artificially synthesized under high pressure in a temperature difference method, characterized in that said diamond has a crystal containing nitrogen in

- an amount of at most 3 ppm and the tool has a blade with an end having a plane orientation being a (110) plane and said crystal also contains nickel.
- 6. (Original) The diamond tool according to claim 5, wherein said nickel is contained in an amount of at least 0.01 ppm and at most 10 ppm.
- 7. (Currently amended) The diamond tool according to claim 5,
 wherein a titanium containing, activated brazing material
 [[(22)]] is employed to attach said diamond to a main body
 of the tool.
- 1 8. (Previously presented) A diamond tool fabricated with a
 2 single crystal diamond artificially synthesized under high
 3 pressure in a temperature difference method, characterized
 4 in that said diamond has a crystal containing nitrogen in
 5 an amount of at most 3 ppm and the tool has a blade with an
 6 end having a plane orientation being a (110) plane and said
 7 crystal also contains boron and nickel.
- 9. (Original) The diamond tool according to claim 8, wherein said boron is contained in an amount of at least 0.01 ppm and at most 300 ppm.
- 1 10. (Original) The diamond tool according to claim 8, wherein said nickel is contained in an amount of at least 0.01 ppm and at most 10 ppm.

- 1 11. (Currently amended) The diamond tool according to claim 8,

 wherein a titanium containing, activated brazing material

 [[(22)]] is employed to attach said diamond to a main body

 of the tool.
- 1 12. (Original) A synthetic single crystal diamond synthesized
 2 under ultra high pressure at high temperature in a
 3 temperature difference method, characterized by having a
 4 crystal containing nickel as a substitutional atom.
- 1 13. (Original) The synthetic single crystal diamond according
 2 to claim 12, wherein said nickel is contained in an amount
 3 of at least 0.01 ppm and at most 10 ppm.
- 1 14. (Original) The synthetic single crystal diamond according
 2 to claim 12, containing nitrogen in an amount of at least
 3 0.01 ppm and at most 3 ppm.
- 1 15. (Original) The synthetic single crystal diamond according to claim 12, used for a tool.
- 1 16. (Currently amended) The synthetic single crystal diamond
 2 according to claim 15, wherein a titanium containing,
 3 activated brazing material [[(22)]] is employed to attach
 4 the synthetic single crystal diamond to an end [[(23)]] of
 5 said tool.

- 1 17. (Original) The synthetic single crystal diamond according to claim 12, used for jewelry.
- 1 18. (Original) A diamond tool comprising the synthetic single crystal diamond of claim 12.
- 1 19. (Original) Diamond jewelry comprising the synthetic single crystal diamond of claim 12.
- 1 20. (Original) A method of synthesizing a single crystal
 2 diamond under ultra high pressure at high temperature in a
 3 temperature difference method, characterized by employing
 4 a solvent formed of at least one of iron and cobalt, at
 5 least 36% by weight of nickel, at least 1% by weight and at
 6 most 2% by weight of titanium, and at least 3% by weight
 7 and at most 5.5% by weight of graphite.
- 21. (Currently amended) The method according to claim 20, wherein a seed face of a seed crystal [[(13)]] is a (100) plane of a crystal of diamond.
- 22. (Original) The method according to claim 20, wherein said single crystal diamond is synthesized at 1380 ± 25°C.
- 1 23. (Original) The method according to claim 20, wherein said 2 single crystal diamond is synthesized at a rate of at least 3 3.9 mg/hr and at most 4.7 mg/hr.

- 1 24. (Original) A synthetic single crystal diamond synthesized
 2 under ultra high pressure at high temperature in a
 3 temperature difference method, characterized by having a
 4 crystal containing boron and nickel as substitutional
 5 atoms.
- 25. (Original) The synthetic single crystal diamond according to claim 24, wherein said boron is contained in an amount of at least 1 ppm and at most 300 ppm.
- 1 **26.** (Original) The synthetic single crystal diamond according to claim 24, wherein said nickel is contained in an amount of at least 0.01 ppm and at most 10 ppm.
- 27. (Original) The synthetic single crystal diamond according to claim 24, containing nitrogen in an amount of at most 3 ppm.
- 1 28. (Original) The synthetic single crystal diamond according to claim 24, used for a tool.
- (Currently amended) The synthetic single crystal diamond according to claim 28, wherein a titanium containing, activated brazing material [[(22)]] is employed to attach the synthetic single crystal diamond to an end [[(23)]] of said tool.

- 30. (Original) The synthetic single crystal diamond according to claim 24, used for jewelry.
- 31. (Original) A diamond tool comprising the synthetic single crystal diamond of claim 24.
- 1 **32.** (Original) Diamond jewelry comprising the synthetic single crystal diamond of claim 24.
- 33. (Original) A method of synthesizing a single crystal 1 2 diamond under ultra high pressure at high temperature in a temperature difference method, characterized by employing 3 a solvent formed of at least one of iron and cobalt, at least 36% by weight of nickel, at least 1% by weight and at 5 most 2% by weight of titanium, at least 0.1% by weight and 6 at most 0.2% by weight of boron and at least 3% by weight 7 and at most 5.5% by weight of graphite. 8
- 1 34. (Currently amended) The method according to claim 33,
 2 wherein a seed face of a seed crystal [[(13)]] is a (100)
 3 plane of a crystal of diamond.
- 1 **35.** (Original) The method according to claim 33, wherein said single crystal diamond is synthesized at 1350 ± 30°C.
- 1 **36.** (Original) The method according to claim 33, wherein said single crystal diamond is synthesized at a rate of at least 3.1 mg/hr and at most 3.8 mg/hr.